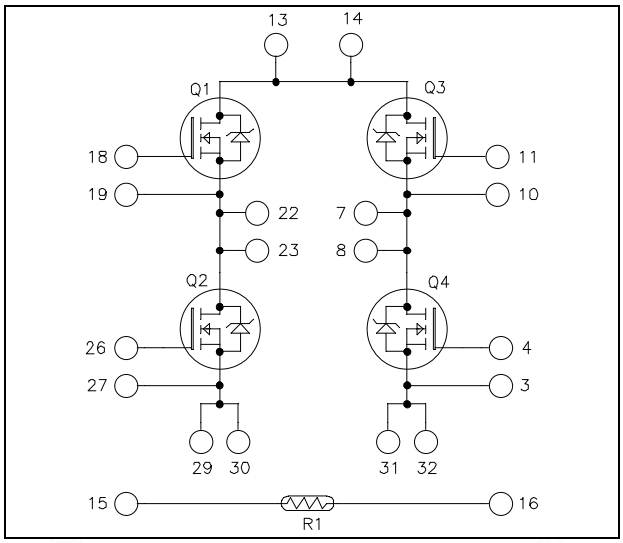
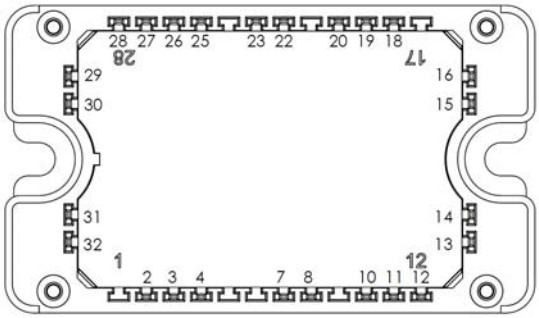
# APTM100H46FT3G

## *Full bridge MOSFET Power Module*

**$V_{DSS}$ = 1000V**
**$R_{DSon}$ = 460mΩ typ @ Tj = 25°C**
**$I_D$ = 19A @ Tc = 25°C**




All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 …

**Application**

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

**Features**

- **Power MOS 8™ Fast FREDFETs**
  - Low $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic reverse diode
  - Avalanche energy rated
  - Very rugged
- Very low stray inductance
- Kelvin source for easy drive
- Internal thermistor for temperature monitoring

**Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

**All ratings @ $T_j$ = 25°C unless otherwise specified**

### Absolute maximum ratings

| *Symbol* | *Parameter* | | *Max ratings* | *Unit* |
|---|---|---|---|---|
| $V_{DSS}$ | Drain - Source Voltage | | 1000 | V |
| $I_D$ | Continuous Drain Current | $T_c$ = 25°C | 19 | A |
| | | $T_c$ = 80°C | 14 | |
| $I_{DM}$ | Pulsed Drain current | | 120 | |
| $V_{GS}$ | Gate - Source Voltage | | ±30 | V |
| $R_{DSon}$ | Drain - Source ON Resistance | | 552 | mΩ |
| $P_D$ | Power Dissipation | $T_c$ = 25°C | 357 | W |
| $I_{AR}$ | Avalanche current (repetitive and non repetitive) | | 16 | A |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

## Electrical Characteristics

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 1000V ; $V_{GS}$ = 0V | | | 250 | µA |
| $R_{DS(on)}$ | Drain – Source on Resistance | $V_{GS}$ = 10V, $I_D$ = 16A | | 460 | 552 | mΩ |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{GS}$ = $V_{DS}$, $I_D$ = 2.5mA | 3 | 4 | 5 | V |
| $I_{GSS}$ | Gate – Source Leakage Current | $V_{GS}$ = ±30 V | | | ±150 | nA |

## Dynamic Characteristics

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $C_{iss}$ | Input Capacitance | $V_{GS}$ = 0V<br>$V_{DS}$ = 25V<br>f = 1MHz | | 6800 | | pF |
| $C_{oss}$ | Output Capacitance | | | 715 | | |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 92 | | |
| $Q_g$ | Total gate Charge | $V_{GS}$ = 10V<br>$V_{Bus}$ = 500V<br>$I_D$ = 16A | | 260 | | nC |
| $Q_{gs}$ | Gate – Source Charge | | | 46 | | |
| $Q_{gd}$ | Gate – Drain Charge | | | 125 | | |
| $T_{d(on)}$ | Turn-on Delay Time | **Resistive switching @ 25°C**<br>$V_{GS}$ = 15V<br>$V_{Bus}$ = 667V<br>$I_D$ = 16A<br>$R_G$ = 2.2Ω | | 36 | | ns |
| $T_r$ | Rise Time | | | 37 | | |
| $T_{d(off)}$ | Turn-off Delay Time | | | 140 | | |
| $T_f$ | Fall Time | | | 35 | | |
| $R_{thJC}$ | Junction to Case Thermal Resistance | | | | 0.35 | °C/W |

## Source - Drain diode ratings and characteristics

| Symbol | Characteristic | Test Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $I_S$ | Continuous Source current (Body diode) | | Tc = 25°C | | | 19 | A |
| | | | Tc = 80°C | | | 14 | |
| $V_{SD}$ | Diode Forward Voltage | $V_{GS}$ = 0V, $I_S$ = - 16A | | | | 1 | V |
| dv/dt | Peak Diode Recovery ❶ | | | | | 25 | V/ns |
| $t_{rr}$ | Reverse Recovery Time | $I_S$ = - 16A<br>$V_R$ = 100V<br>$di_S/dt$ = 100A/µs | $T_j$ = 25°C | | | 290 | ns |
| | | | $T_j$ = 125°C | | | 600 | |
| $Q_{rr}$ | Reverse Recovery Charge | | $T_j$ = 25°C | | 1.3 | | µC |
| | | | $T_j$ = 125°C | | 3.5 | | |

❶ dv/dt numbers reflect the limitations of the circuit rather than the device itself.
$I_S \leq$ - 16A  di/dt ≤ 1000A/µs  $V_{DD} \leq$ 667V  $T_j \leq$ 125°C

## Thermal and package characteristics

| Symbol | Characteristic | | | Min | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{ISOL}$ | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz | | | 4000 | | V |
| $T_J$ | Operating junction temperature range | | | -40 | 150 | °C |
| $T_{JOP}$ | Recommended junction temperature under switching conditions | | | -40 | $T_J$max - 25 | |
| $T_{STG}$ | Storage Temperature Range | | | -40 | 125 | |
| $T_C$ | Operating Case Temperature | | | -40 | 125 | |
| Torque | Mounting torque | To heatsink | M4 | 2 | 3 | N.m |
| Wt | Package Weight | | | | 110 | g |

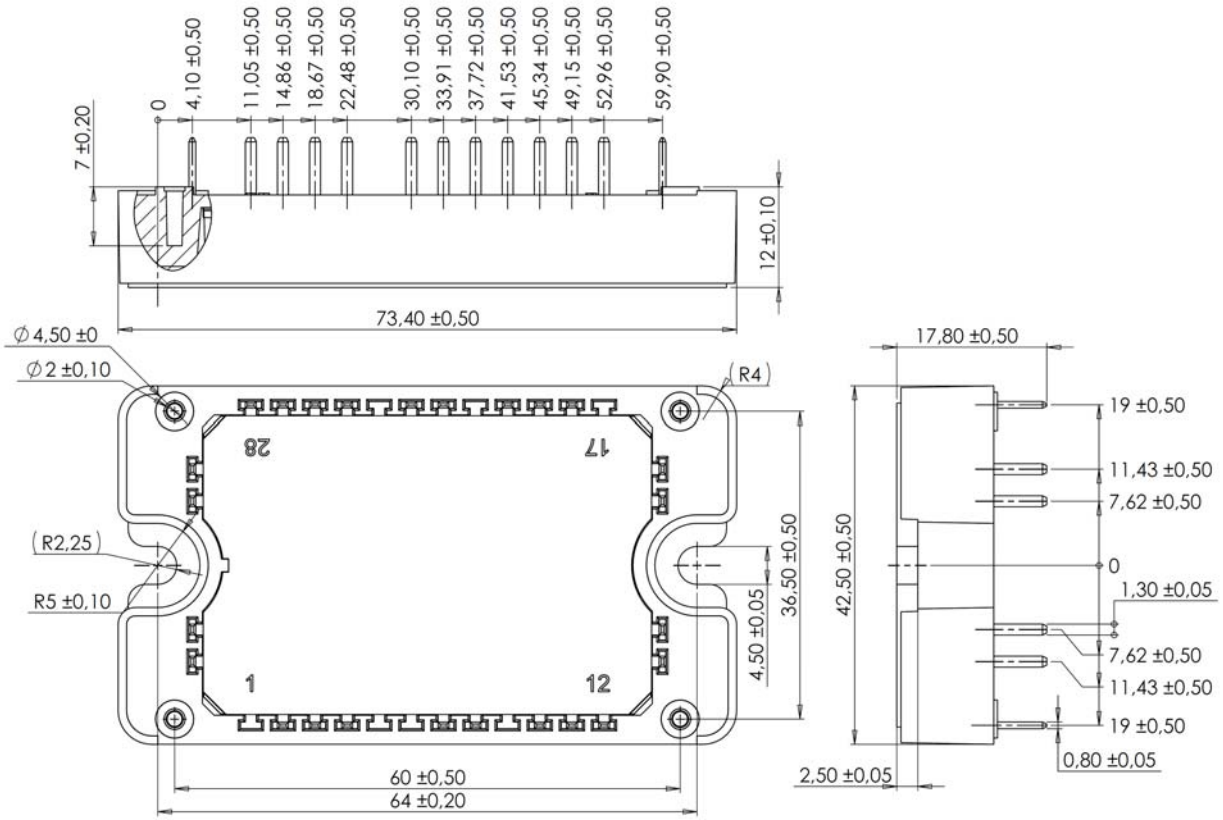
## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

| Symbol | Characteristic | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $R_{25}$ | Resistance @ 25°C | | | 50 | | kΩ |
| $\Delta R_{25}/R_{25}$ | | | | 5 | | % |
| $B_{25/85}$ | $T_{25}$ = 298.15 K | | | 3952 | | K |
| $\Delta B/B$ | | $T_C$=100°C | | 4 | | % |

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
$R_T$: Thermistor value at T

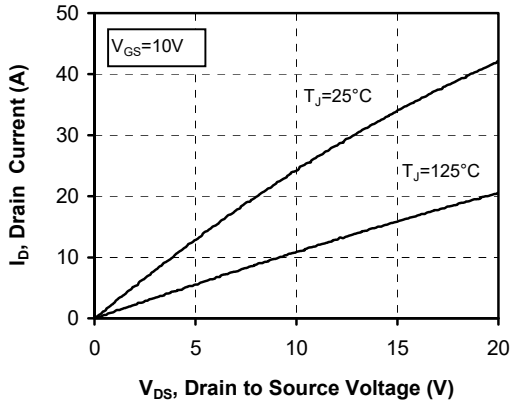
## Package outline (dimensions in mm)



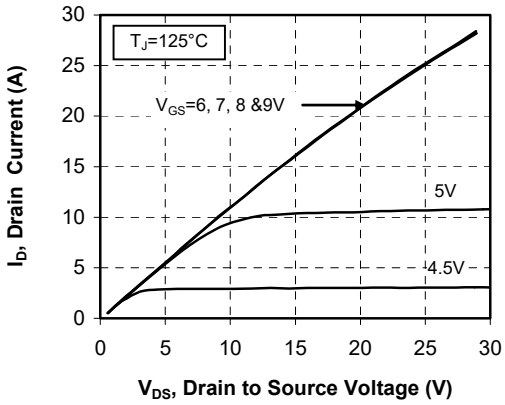

See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

## Typical Performance Curve

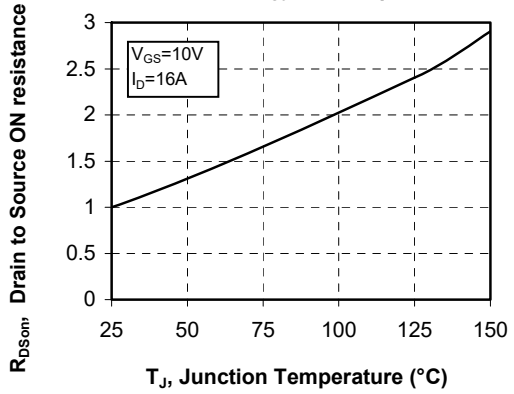
Low Voltage Output Characteristics



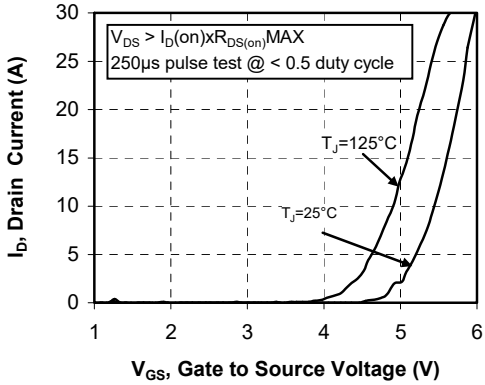

Low Voltage Output Characteristics



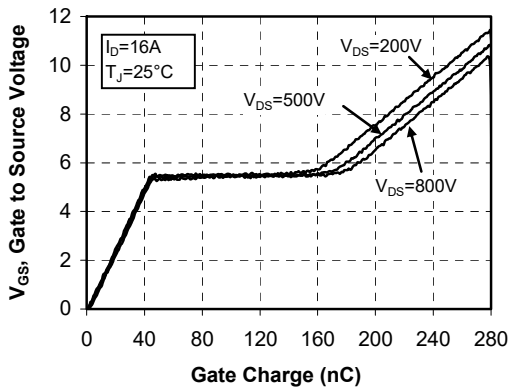

Normalized $R_{DSon}$ vs. Temperature



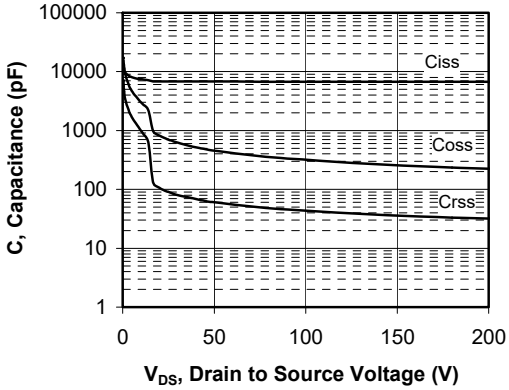

Transfert Characteristics



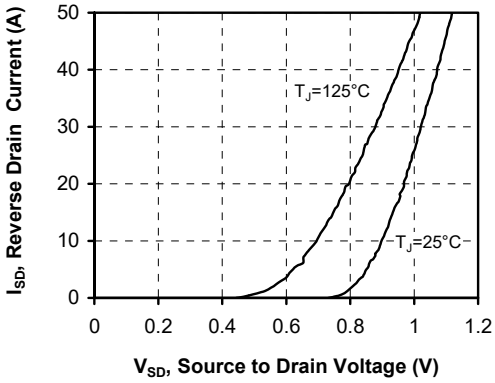

Gate Charge vs Gate to Source



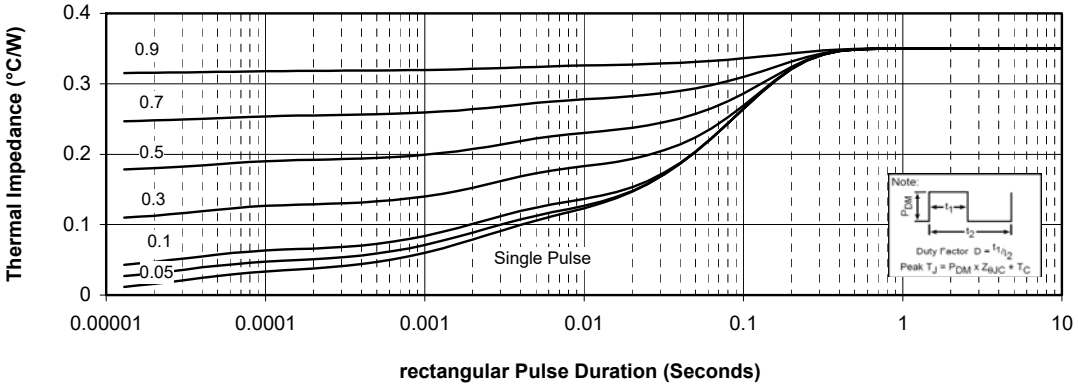

Capacitance vs Drain to Source Voltage



**Drain Current vs Source to Drain Voltage**




**Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration**



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